ABSTRACT OF THE DISCLOSURE

A mask and its application in sequential lateral solidification (SLS) crystallization of amorphous silicon are provided. The mask includes a light absorptive portion for blocking a laser beam and a plurality of stripe-shaped light transmitting portions for passing the laser beam. Each stripe-shaped light transmitting portion is rectangular-shaped, and each light-transmitting portion includes triangular-shaped or semicircular-shaped edges on both sides. The distance between the adjacent light transmitting portions is less than the width of the light transmitting portion. The width of the light transmitting portions is less than or equal to twice the maximum length of lateral grain growth that is to be grown by sequential lateral solidification (SLS).